



Band switching diode

Features

1. Low differential forward resistance
2. Low diode capacitance
3. High reverse impedance

Applications

Band switching in VHF-tuners



Construction

Silicon epitaxial planar

Absolute Maximum Ratings

$T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
DC Reverse voltage		V_R	35	V
Average rectified current		I_O	100	mA
Power dissipation		P_d	150	MW
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-55...+150	$^{\circ}\text{C}$

Stresses exceeding maximum ratings may damage the device. Maximum ratings are stress ratings only. Functional operation above the recommended operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.

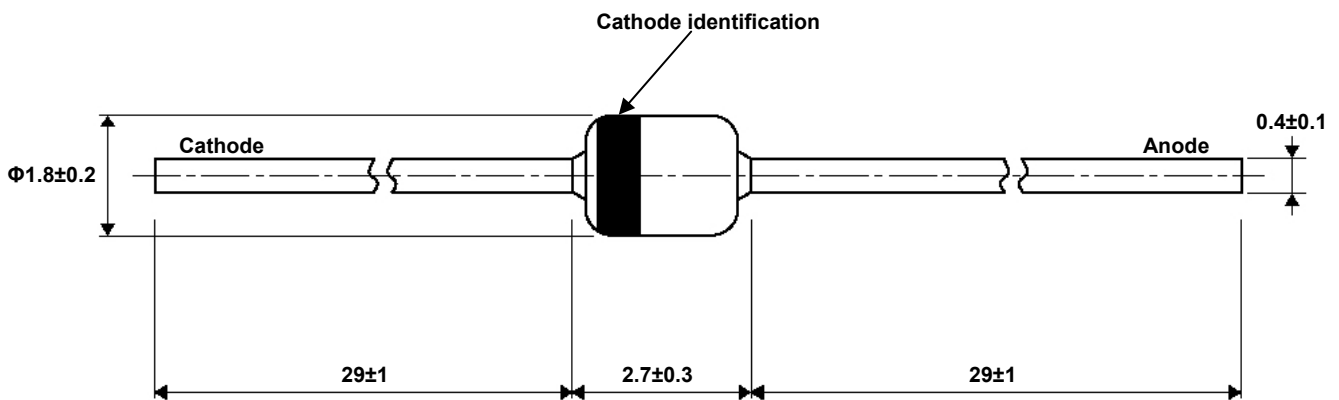


Electrical Characteristics

T_j=25°C

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =10mA	V _F		0.85	1	V
Reverse current	V _R =20V	I _R			100	nA
Breakdown voltage	I _R =10μA	B _V	35			V
Terminal capacitance	f=1MHz, V _R =6V	C _t			1.5	pF
Frequency resistance	f=100MHz, I _F =10mA	r _f			0.6	Ω

Dimensions in mm



Standard Glass Case
JEDEC DO-34